

Refine Search

10/630,969

Search Results -

Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1

Database:

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search:

L6	<input type="button" value="Refine Search"/>
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Search History

DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

<u>Set</u>	<u>Hit</u>	<u>Set</u>
<u>Name</u>	<u>Count</u>	<u>Name</u>
		result set
<u>side by side</u>		
DB=USPT; PLUR=YES; OP=ADJ		
<u>L6</u> L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	1	<u>L6</u>
<u>L5</u> L3 and oxidation	20	<u>L5</u>
<u>L4</u> L3 and oxidation and (sio2)	0	<u>L4</u>
<u>L3</u> L2 and (inert or argon or ar or helium or he or neon or ne or kr or krypton or xenon or nitrogen)	45	<u>L3</u>
<u>L2</u> L1 and ((ratio) near3 (nitrogen and oxygen))	45	<u>L2</u>
<u>L1</u> microstructure	23090	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Search Results - Record(s) 1 through 1 of 1 returned.

1. Document ID: US 6071601 A

L6: Entry 1 of 1

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Terms	Documents
L5 and (hfo2 or zro2 or ta2o5 or tio2 or aL2o3 or hfsio)	1

Display Format:

[Previous Page](#) [Next Page](#) [Go to Doc#](#)

Refine Search

Search Results -

Terms	Documents
L5 and pressure and torr	5

Database:	US Pre-Grant Publication Full-Text Database US Patents Full-Text Database US OCR Full-Text Database EPO Abstracts Database JPO Abstracts Database Derwent World Patents Index IBM Technical Disclosure Bulletins
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Search:	<input style="width: 100%; height: 25px; border: 1px solid black; padding: 2px; font-size: 0.8em; border-collapse: collapse;" type="text" value="L7"/>	<input style="width: 100%; height: 25px; border: 1px solid black; padding: 2px; font-size: 0.8em; border-collapse: collapse;" type="button" value="Refine Search"/>	
	<input style="width: 100px; height: 20px; border: 1px solid black; padding: 2px; font-size: 0.8em; border-collapse: collapse;" type="button" value="Recall Text"/>	<input style="width: 100px; height: 20px; border: 1px solid black; padding: 2px; font-size: 0.8em; border-collapse: collapse;" type="button" value="Clear"/>	<input style="width: 100px; height: 20px; border: 1px solid black; padding: 2px; font-size: 0.8em; border-collapse: collapse;" type="button" value="Interrupt"/>

Search History

DATE: **Tuesday, June 29, 2004** [Printable Copy](#) [Create Case](#)

Set	Name	Query			
Set	Name	Query	Count	Hit	Set
side by side					
DB=USPT; PLUR=YES; OP=ADJ					
<u>L7</u>	L5 and pressure and torr		5	<u>L7</u>	
<u>L6</u>	L5 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)		1	<u>L6</u>	
<u>L5</u>	L3 and oxidation		20	<u>L5</u>	
<u>L4</u>	L3 and oxidation and (sio2)		0	<u>L4</u>	
<u>L3</u>	L2 and (inert or argon or ar or helium or he or neon or ne or kr or krypton or xenon or nitrogen)		45	<u>L3</u>	
<u>L2</u>	L1 and ((ratio) near3 (nitrogen and oxygen))		45	<u>L2</u>	
<u>L1</u>	microstructure		23090	<u>L1</u>	

END OF SEARCH HISTORY

Hit List

[Clear](#) [Generate Collection](#) [Print](#) [Fwd Refs](#) [Bkwd Refs](#)
[Generate OACS](#)

Search Results - Record(s) 1 through 5 of 5 returned.

1. Document ID: US 6498097 B1

L7: Entry 1 of 5

File: USPT

Dec 24, 2002

US-PAT-NO: 6498097

DOCUMENT-IDENTIFIER: US 6498097 B1

TITLE: Apparatus and method of forming preferred orientation-controlled platinum film using oxygen

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn D](#)

2. Document ID: US 6071601 A

L7: Entry 2 of 5

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn D](#)

3. Document ID: US 6054331 A

L7: Entry 3 of 5

File: USPT

Apr 25, 2000

US-PAT-NO: 6054331

DOCUMENT-IDENTIFIER: US 6054331 A

TITLE: Apparatus and methods of depositing a platinum film with anti-oxidizing function over a substrate

[Full](#) [Title](#) [Citation](#) [Front](#) [Review](#) [Classification](#) [Date](#) [Reference](#) [Claims](#) [KMC](#) [Drawn D](#)

4. Document ID: US 5143879 A

L7: Entry 4 of 5

File: USPT

Sep 1, 1992

US-PAT-NO: 5143879

DOCUMENT-IDENTIFIER: US 5143879 A
** See image for Certificate of Correction **

TITLE: Method to recover organic templates from freshly synthesized molecular sieves

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Abstract](#) | [Claims](#) | [KMC](#) | [Drawn](#) | [Cited](#)

5. Document ID: US 4762728 A

L7: Entry 5 of 5

File: USPT

Aug 9, 1988

US-PAT-NO: 4762728

DOCUMENT-IDENTIFIER: US 4762728 A

TITLE: Low temperature plasma nitridation process and applications of nitride films formed thereby

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Abstract](#) | [Claims](#) | [KMC](#) | [Drawn](#) | [Cited](#)

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Terms	Documents
L5 and pressure and torr	5

Display Format: [Change Format](#)

[Previous Page](#) [Next Page](#) [Go to Doc#](#)

Hit List

10/6/30, 969

Clear **Generate Collection** **Print** **Fwd Refs** **Bkwd Refs**
Generate OACS

Search Results - Record(s) 1 through 4 of 4 returned.**□ 1. Document ID: US 6548343 B1**

L24: Entry 1 of 4

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

Full **Title** **Citation** **Front** **Review** **Classification** **Date** **Reference** **Claims** **KMC** **Draw** **De**

□ 2. Document ID: US 6485988 B2

L24: Entry 2 of 4

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

Full **Title** **Citation** **Front** **Review** **Classification** **Date** **Reference** **Claims** **KMC** **Draw** **De**

□ 3. Document ID: US 6413386 B1

L24: Entry 3 of 4

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full **Title** **Citation** **Front** **Review** **Classification** **Date** **Reference** **Claims** **KMC** **Draw** **De**

□ 4. Document ID: US 6362093 B1

L24: Entry 4 of 4

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Search](#) | [Help](#) | [Claims](#) | [KWMC](#) | [Drawn](#) | [Text](#)

[Clear](#)

[Generate Collection](#)

[Print](#)

[Fwd Refs](#)

[Bkwd Refs](#)

[Generate GACS](#)

Terms	Documents
L23 and (silicon adj oxynitride)	4

Display Format:

[Change Format](#)

[Previous Page](#)

[Next Page](#)

[Go to Doc#](#)

Refine Search

Search Results -

Terms	Documents
L23 and (silicon adj oxynitride)	4

Database:

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 EPO Abstracts Database
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 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L24

Search History

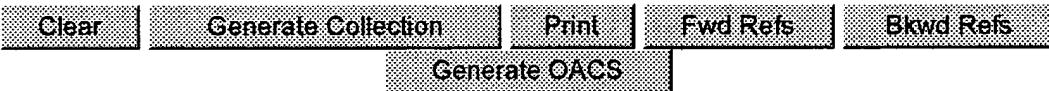
DATE: Tuesday, June 29, 2004 [Printable Copy](#) [Create Case](#)

<u>Set</u> <u>Name</u> <u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
side by side		
DB=USPT; PLUR=YES; OP=ADJ		
<u>L24</u> L23 and (silicon adj oxynitride)	4	<u>L24</u>
<u>L23</u> L22 and (silicon adj oxide)	7	<u>L23</u>
<u>L22</u> L21 and oxide and (oxygen adj containing)	11	<u>L22</u>
<u>L21</u> L20 and semiconductor and (flow adj rate)	80	<u>L21</u>
<u>L20</u> L19 and (inert or h2 or ne or ar or xe or neon or argon or krypton or kr)	1159	<u>L20</u>
<u>L19</u> (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	2645	<u>L19</u>
<u>L18</u> L2 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L18</u>
<u>L17</u> L11 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L17</u>
<u>L16</u> L15 and (hfo2 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	0	<u>L16</u>
<u>L15</u> L11 and (inert or argon or neon or hydrogen or xenon or krypton)	56	<u>L15</u>
<u>L14</u> L11 and (inert or argon or neon or hydrogen or xenon or krypton) and (high adj K)	0	<u>L14</u>
<u>L13</u> L11 near10 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L13</u>

<u>L12</u>	L11 near5 ((nitrogen and oxygen) or (n2 and o2))	0	<u>L12</u>
<u>L11</u>	(flow adj rate) near4 (3:1)	76	<u>L11</u>
<u>L10</u>	l2 and (3:1)	8	<u>L10</u>
<u>L9</u>	l2 and (nitrogen:oxygen)	0	<u>L9</u>
<u>L8</u>	n2:o2	2	<u>L8</u>
<u>L7</u>	L4 and (high adj K) and oxidation and chamber	3	<u>L7</u>
<u>L6</u>	L5 and (silicon adj oxide)	9	<u>L6</u>
<u>L5</u>	L4 and (oxygen adj containing)	19	<u>L5</u>
<u>L4</u>	L2 and nitrogen and oxygen and (inert or hydrogen or argon or h2 or ar or xenon or xe or krypton or kr or neon or ne)	88	<u>L4</u>
<u>L3</u>	L2 and ((nitrogen and oxygen) near2 (ratio))	3	<u>L3</u>
<u>L2</u>	(semiconductor or wafer) and (micro) and (flow near ratio)	231	<u>L2</u>
<u>L1</u>	microstructure near5 (flow ratio)	2	<u>L1</u>

END OF SEARCH HISTORY

Hit List



Search Results - Record(s) 1 through 7 of 7 returned.

1. Document ID: US 6620670 B2

L23: Entry 1 of 7

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of AL2O3

2. Document ID: US 6583463 B1

L23: Entry 2 of 7

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized TA2O5 capacitor insulator

3. Document ID: US 6548343 B1

L23: Entry 3 of 7

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343

DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell



4. Document ID: US 6544875 B1

L23: Entry 4 of 7

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875

DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)**5. Document ID: US 6485988 B2**

L23: Entry 5 of 7

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988

DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)**6. Document ID: US 6413386 B1**

L23: Entry 6 of 7

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386

DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)**7. Document ID: US 6362093 B1**

L23: Entry 7 of 7

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

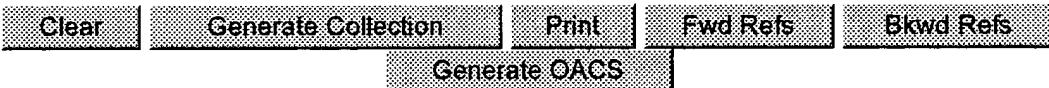
[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KMC](#) | [Draw](#)[Clear](#) | [Generate Collection](#) | [Print](#) | [Fwd Refs](#) | [Bkwd Refs](#) | [Generate OACS](#)

Terms	Documents
L22 and (silicon adj oxide)	7

Display Format:

[Previous Page](#) [Next Page](#) [Go to Doc#](#)

Hit List



Search Results - Record(s) 1 through 10 of 11 returned.

1. Document ID: US 6659111 B1

L22: Entry 1 of 11

File: USPT

Dec 9, 2003

US-PAT-NO: 6659111

DOCUMENT-IDENTIFIER: US 6659111 B1

TITLE: Cleaning gas and method for cleaning vacuum treatment apparatus by flowing the cleaning gas



2. Document ID: US 6620670 B2

L22: Entry 2 of 11

File: USPT

Sep 16, 2003

US-PAT-NO: 6620670

DOCUMENT-IDENTIFIER: US 6620670 B2

TITLE: Process conditions and precursors for atomic layer deposition (ALD) of Al2O3

3. Document ID: US 6583463 B1

L22: Entry 3 of 11

File: USPT

Jun 24, 2003

US-PAT-NO: 6583463

DOCUMENT-IDENTIFIER: US 6583463 B1

TITLE: Semiconductor integrated circuit device with information storage capacitor having ruthenium dioxide lower electrode and crystallized Ta2O5 capacitor insulator

4. Document ID: US 6548343 B1

L22: Entry 4 of 11

File: USPT

Apr 15, 2003

US-PAT-NO: 6548343
DOCUMENT-IDENTIFIER: US 6548343 B1

TITLE: Method of fabricating a ferroelectric memory cell

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

5. Document ID: US 6544875 B1

L22: Entry 5 of 11

File: USPT

Apr 8, 2003

US-PAT-NO: 6544875
DOCUMENT-IDENTIFIER: US 6544875 B1

TITLE: Chemical vapor deposition of silicate high dielectric constant materials

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

6. Document ID: US 6509511 B1

L22: Entry 6 of 11

File: USPT

Jan 21, 2003

US-PAT-NO: 6509511
DOCUMENT-IDENTIFIER: US 6509511 B1

TITLE: Process for the conversion of perfluoroalkanes, a catalyst for use therein and a method for its preparation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

7. Document ID: US 6485988 B2

L22: Entry 7 of 11

File: USPT

Nov 26, 2002

US-PAT-NO: 6485988
DOCUMENT-IDENTIFIER: US 6485988 B2

TITLE: Hydrogen-free contact etch for ferroelectric capacitor formation

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Claims](#) | [KINIC](#) | [Drawn](#)

8. Document ID: US 6413386 B1

L22: Entry 8 of 11

File: USPT

Jul 2, 2002

US-PAT-NO: 6413386
DOCUMENT-IDENTIFIER: US 6413386 B1

TITLE: Reactive sputtering method for forming metal-silicon layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Drawn D
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□ 9. Document ID: US 6362093 B1

L22: Entry 9 of 11

File: USPT

Mar 26, 2002

US-PAT-NO: 6362093

DOCUMENT-IDENTIFIER: US 6362093 B1

TITLE: Dual damascene method employing sacrificial via fill layer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Drawn D
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□ 10. Document ID: US 6238582 B1

L22: Entry 10 of 11

File: USPT

May 29, 2001

US-PAT-NO: 6238582

DOCUMENT-IDENTIFIER: US 6238582 B1

TITLE: Reactive ion beam etching method and a thin film head fabricated using the method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Drawn D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate GACS
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Terms	Documents
L21 and oxide and (oxygen adj containing)	11

Display Format: [Previous Page](#)[Next Page](#)[Go to Doc#](#)

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 11 through 11 of 11 returned.

□ 11. Document ID: US 6218300 B1

L22: Entry 11 of 11

File: USPT

Apr 17, 2001

US-PAT-NO: 6218300

DOCUMENT-IDENTIFIER: US 6218300 B1

TITLE: Method and apparatus for forming a titanium doped tantalum pentaoxide dielectric layer using CVD

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KIMC	Draw	D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L21 and oxide and (oxygen adj containing)	11

Display Format: [Change Format](#)

[Previous Page](#) [Next Page](#) [Go to Doc#](#)

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 3 of 3 returned.

1. Document ID: US 6387819 B1

L3: Entry 1 of 3

File: USPT

May 14, 2002

US-PAT-NO: 6387819

DOCUMENT-IDENTIFIER: US 6387819 B1

TITLE: Method for etching low K dielectric layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KINIC	Drawn
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2. Document ID: US 6110609 A

L3: Entry 2 of 3

File: USPT

Aug 29, 2000

US-PAT-NO: 6110609

DOCUMENT-IDENTIFIER: US 6110609 A

TITLE: Magnetic thin film and magnetic head using the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KINIC	Drawn
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3. Document ID: US 4543707 A

L3: Entry 3 of 3

File: USPT

Oct 1, 1985

US-PAT-NO: 4543707

DOCUMENT-IDENTIFIER: US 4543707 A

TITLE: Method of forming through holes by differential etching of stacked silicon oxynitride layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KINIC	Drawn
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L2 and ((nitrogen and oxygen) near2 (ratio))	3

Display Format: [Change Format](#)

[Previous Page](#) [Next Page](#) [Go to Doc#](#)